

**5HP01N**

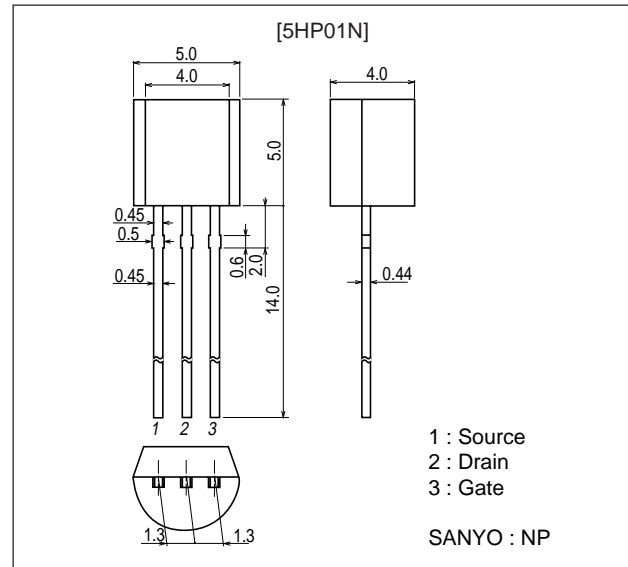
Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Package Dimensions

unit : mm
2178



Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-50	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		-0.07	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycles $\leq 1\%$	-0.28	A
Allowable Power Dissipation	P_D		0.4	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics

 at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}$, $V_{GS} = 0$	-50			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -50\text{V}$, $V_{GS} = 0$			-10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16\text{V}$, $V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}$, $I_D = -100\mu\text{A}$	-1		-2.5	V

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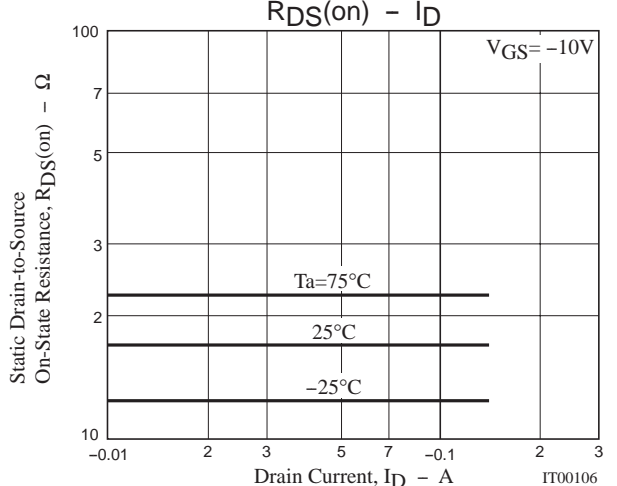
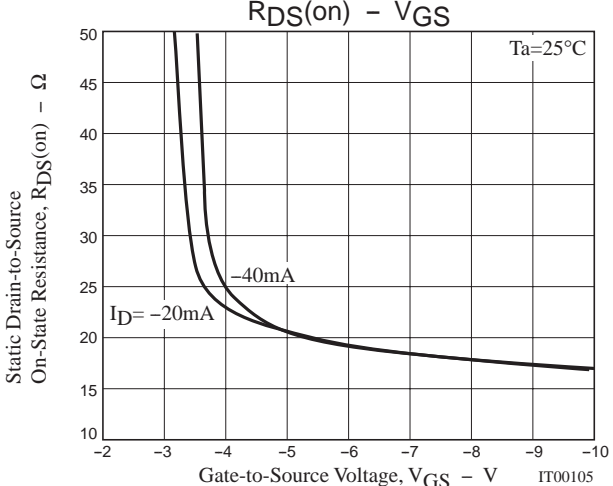
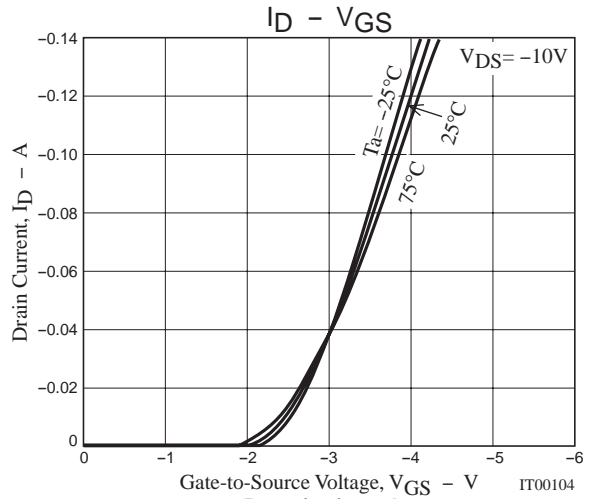
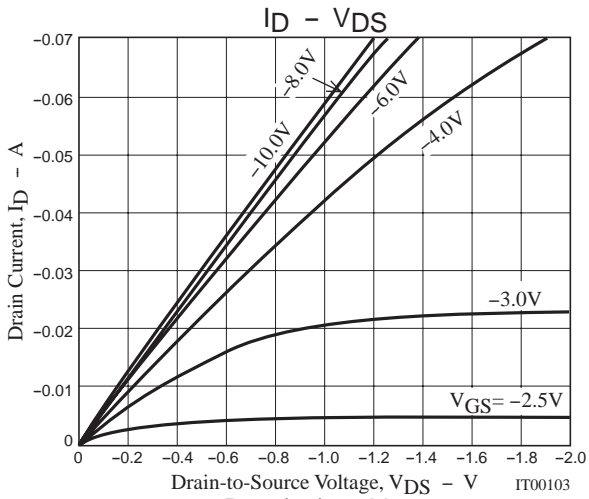
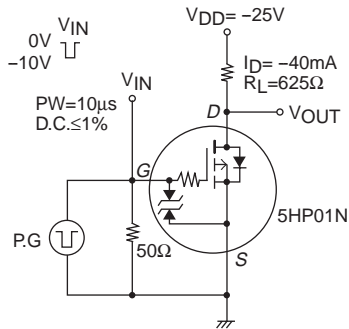
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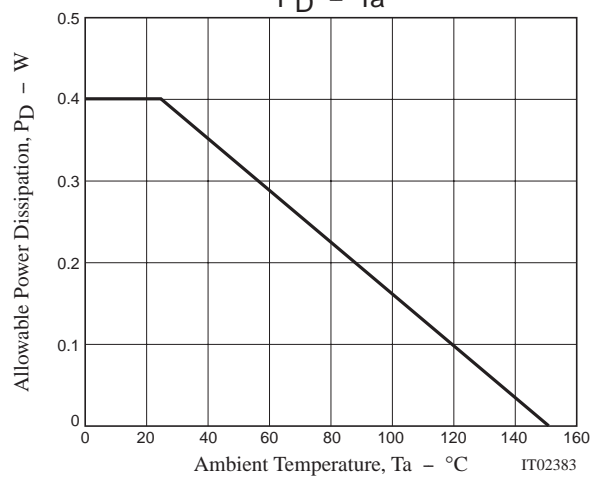
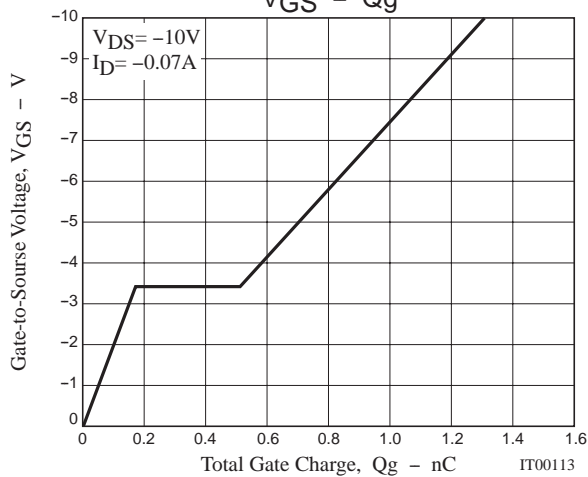
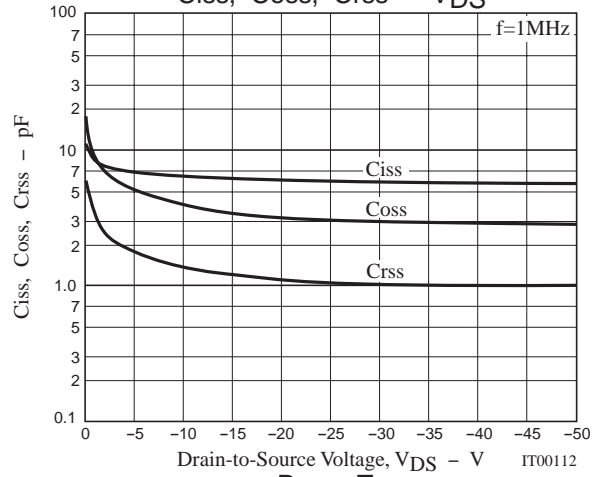
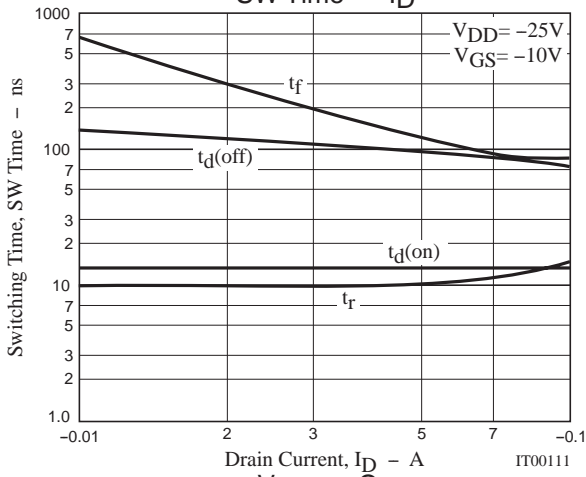
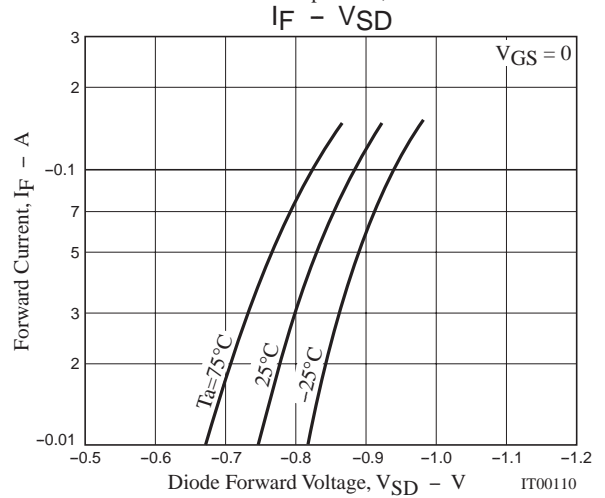
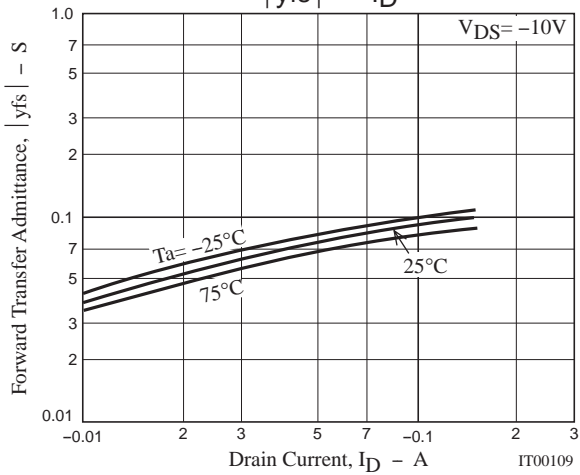
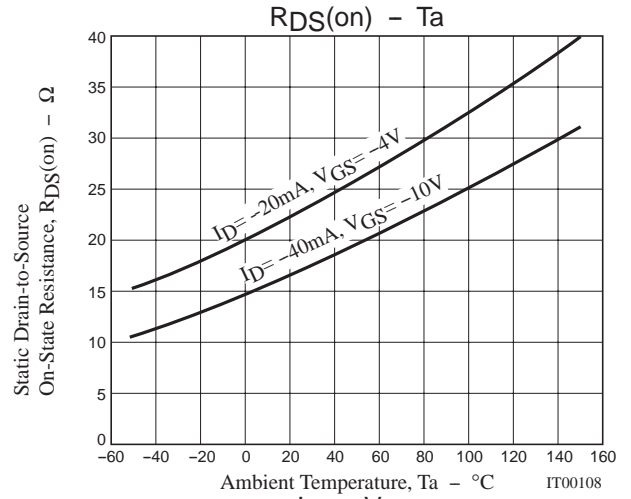
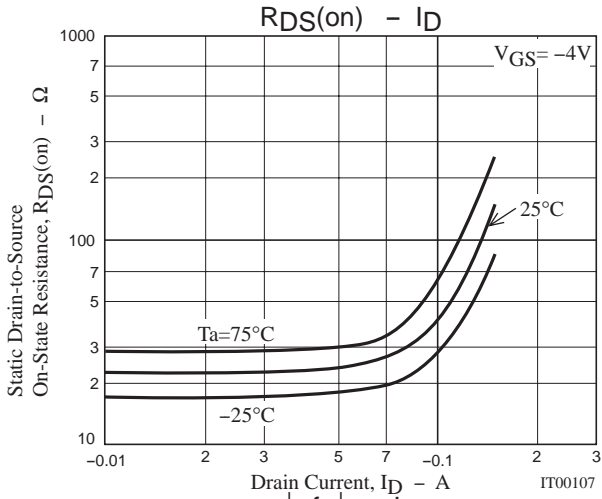
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10V, I_D=-40mA$	50	70		mS
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-40mA, V_{GS}=-10V$		17	22	Ω
	$R_{DS(on)2}$	$I_D=-20mA, V_{GS}=-4V$		23	32	Ω
Input Capacitance	C_{iss}	$V_{DS}=-10V, f=1MHz$		6.2		pF
Output Capacitance	C_{oss}	$V_{DS}=-10V, f=1MHz$		4.0		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-10V, f=1MHz$		1.3		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		13		ns
Rise Time	t_r	See specified Test Circuit		10		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit		100		ns
Fall Time	t_f	See specified Test Circuit		150		ns
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-10V, I_D=-70mA$		1.32		nC
Gate Source Charge	Q_{gs}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-70mA$		0.17		nC
Gate Drain Charge	Q_{gd}	$V_{DS}=-10V, V_{GS}=-10V, I_D=-70mA$		0.34		nC
Diode Forward Voltage	V_{SD}	$I_S=-70mA, V_{GS}=0$		0.85	1.2	V

Marking : XC

Switching Time Test Circuit



5HP01N



Note on usage : Since the 5HP01N is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.

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